

ABSTRACT OF THE DISCLOSURE

For suppressing decomposition of organic group (for example, CH₃ group) during ashing process, which is bonded to Si atom of an organic SOG film or layer for use in flattening process, a method
5 comprises following steps: forming an organic SOG layer directly or through a predetermined film including a hillock protection layer on said lower wiring layer; forming said upper wiring layer on said organic SOG layer without processing of etching back;
10 forming a via hole through an etching process by using a patterned resist layer provided on said upper wiring layer as a mask; performing ashing process with a plasma by making ion or radical which is induced from oxygen gas as a main reactant, under an atmosphere of pressure ranging from 0.01 Torr to 30.0 Torr; and
15 burying said via hole with conductive material so as to electrically connect between said lower wiring layer and said upper wiring layer.

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